High-speed Switching Transistor

2SA1952 / 2SA1906 / 2SA1757

●Features

- 1) High speed switching (tf: Typ. 0.15 μ s at Ic=-3A)
- 2) Low VcE(sat). (Typ.-0.2V at Ic/Is=-3/-0.15A)
- 3) Wide SOA (safe operating area)
- 4) Complements the 2SC5103/2SC4596.

●Packaging specifications and hre

Туре	2SA1952	2SA1906	2SA1757
Package	CPT3	PSD3	TO-220FP
hee	Q	DEF	F
Code	TL	TL	_
Basic ordering unit (pieces)	3000	1000	500

●Absolute maximum ratings (Ta=25℃)

Parameter		Symbol	Limits	Unit
Collector-base voltage		Vcвo	-100	V
Collector-er	nitter voltage	Vceo	-60	V
Emitter-bas	e voltage	VEBQ	-5	V
C-11	Collector current		5	A
Collector ou			-10	A (Pulse)
Collector	2SA1757		2	W
power	2SA1952	Pc	10	W(Tc=25°C)
dissipation 2SA1757, 2SA1906			25	W(10-25C)
Junction temperature		Tj	150	°C
Storage temperature		Tstg	−55~150	°C

●Electrical characteristics (Ta=25°C)

Param	eter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base brea	kdown voltage	ВУсво	-100	_	_	٧	Ic=-50 μA	
Collector-emitter vo	Itage	BVceo(sus)	60	_	_	٧	lc/ls=-3A/-0.3A, L=1mH	
Collector-emitter br	eakdown voltage	BVCEO	~-60	_		٧	Ic=-1mA	
Emitter-base break	down voltage	ВУєво	-5	_		٧	I _E =-50 μA	
Collector cutoff curi	ent	Ісво		_	10	μA	Vcs=-100V	
Emitter cutoff curre	nt	leso	_	_	-10	μA	V _{EB} =-5V	
		V	_	_	-0.3	V	Ic/Is=-3A/-0.15A	
Collector-emitter sa	ituration voitage	VCE(sat)	_	_	-0.5	٧	Ic/Is=-4A/-0.2A	
		Vocas	_	_	-1.2	V	Ic/Is=-3A/-0.15A	
Base-emitter satura	nion vonage	VBE(sat)	_	_	-1.5	٧	Ic/IB=-4A/-0.2A	
	2SA1952		120		270			
DC current	2SA1906	hre	60	_	320		Vc=-2V , Ic=-1A	
transfer ratio	2SA1757]	160	_	320	_	1	
Transition frequenc	У	fτ	-	80	_	MHz	Vce=-10V , le=0.5A , f=30MHz	
Output capacitance		Cob	_	130		pF	Vcs=-10V, le=0A, f=1MHz	
Turn-on time		ton		_	0.3	μ8	Ic=-3A , RL=10 Ω	
Storage time		tang			1.5	μS	IB1=-IB2=-0.15A	
Fall time		tı	_	_	0.3	μS	7 Vcc≒-30V	

(96-603-A314)

High-speed Switching Transistor

2SC5103 / 2SC4596

●Features

- 1) Low VcE(sat). (Typ. 0.15V at Ic/Is=3/0.15A)
- 2) High speed switching (tf: Typ. 0.1 μs at Ic=3A)
- 3) Wide SOA (safe operating area)
- 4) Complements the 2SA1952/2SA1757.

●Packaging specifications and hre

Туре	2SC5103	2SC4596
Package	CPT3	TO-220FP
hre	PQ	EF
Code	TL	
Basic ordering unit (pieces)	2500	500

●Absolute maximum ratings (Ta=25℃)

Parameter		Symbol	Limits	Unit
Collector-base voltage		Vcso	100	V
Collector-emitter	voltage	VCEO	60	V
Emitter-base volt	age	VEBO	5	V
0-11		lc.	5	A (DC)
Collector current	Collector current		10	A (Pulse) *
	2SC5103	Pc 1	1	w
Collector power			2	7 **
dissipation	2SC4596	— Pc	10	W(Tc=25℃)
	2504596		25	1 W(16-25C)
Junction temperature		Tj	150	°C
Storage temperature		Tstq	-55~150	r

^{*} Single pulse Pw=100ms

●Electrical characteristics (Ta=25℃)

Para	meter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base br	eakdown voltage	ВУсво	100	_	_	V	Ic=50 μ A	
Collector-emitter	voltage	BVCEO(SUS)	60		_	\ V	Ic/Is=3A/0.3A, L=1mH	
Collector-emitter	breakdown voltage	BVceo	60	_		V	lc=1mA	
Emitter-base brea	akdown voltage	ВУево	5		_	V	Iε=50 μA	
Collector cutoff c	urrent	Iceo			10	μA	Vc8=100V	
Emitter cutoff cur	rent	leso	_		10	μĀ	VEB=5V	
•		V	_	0.15	0.3	V	Ic/Is=3A/0.15A	*
Collector-emitter	r saturation voltage VCE(sat)		_	_	0.5	V	Ic/Is=4A/0.2A	*
S		V _{BE} (sat)	_	_	1.2	V	Ic/Is=3A/0.15A	*
Base-emitter satu	ration voltage				1.5	V	Ic/Is=4A/0.2A	*
DC current	2SC5103	hre	82	_	270	—	14-4	
transfer ratio	2SC4596	IIFE	100		320	-	Vce/lc=2V/1A	
Transition freque	ncy	fτ	_	120		MHz	Vcs=10V , IE=0.5A , f=30MHz	*
Output capacitan	се	Cob	_	80	_	pF	Vc=10V, l=0A, f=1MHz	
Turn-on time		ton	_	_	0.3	μ8	Ic=3A , RL=10Ω	
Storage time		tstg		T —	1.5	μs	I _{B1} =-I _{B2} =0.15A	
Fall time		tr		0.1	0.3	μŞ	Vcc≒30V	

* Measured using pulse current.

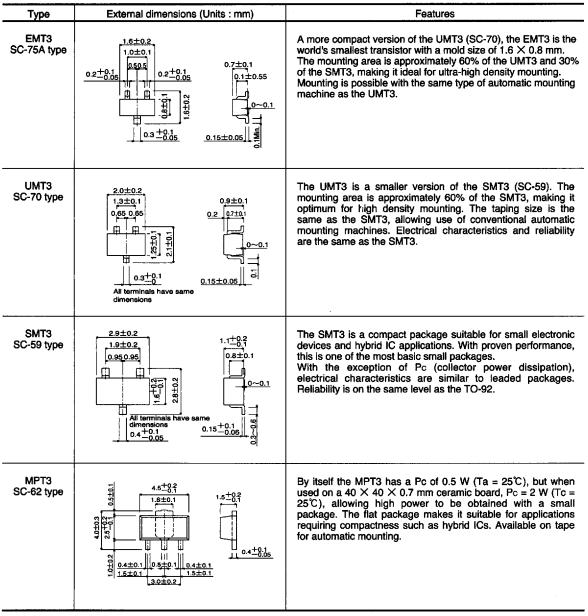
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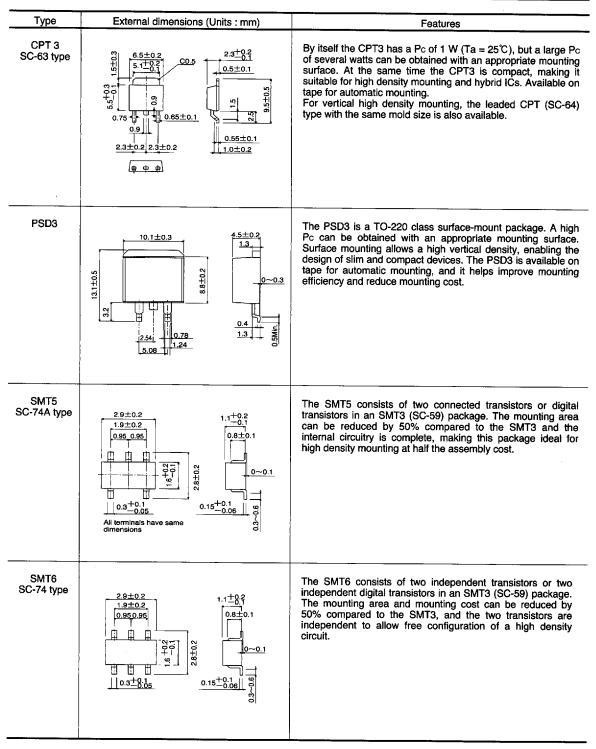
(96-199-C314)

Packages

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.

Types and features of surface-mount packages

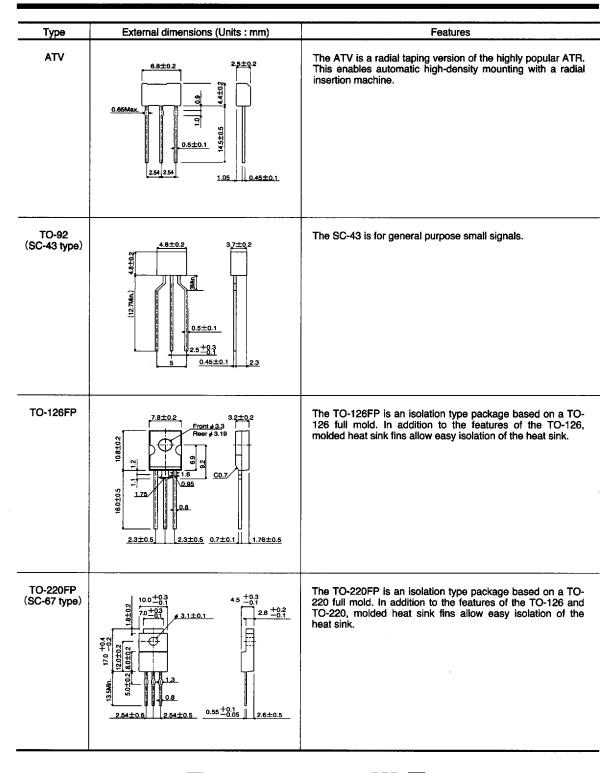




Туре	External dimensions (Units : mm)	Features
UMT5 SC-88A type	2.0±0.2 1,3±0.1 0,65 0,95 1,3±0.1 0,7 1,3±0.1 0,7 1,3±0.1 0,7 1,3±0.1 0,7 1,3±0.1 0,7 1,3±0.1 1,3±0.1 1,0,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0 1,0	The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost.
UMT6 SC-88 type	2.0±0.2 1,3±0.1 0.65 0.65 0.7 0.7 0.7 0.7 0.7 0.7 0.7 0.7	The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit.

●Types and features of leaded packages

Туре	External dimensions (Units : mm)	Features
SPT (SC-72 type)	2±0,2 0.45±0.15 0.45±0.15 0.5 0.45±0.15 0.5 0.45±0.15	The SPT is a smaller version of the conventional TO-92 type. The body size (3×4×2 mm³) has been reduced to 1/4 that of the TO-92 (5×5×4 mm³). The SPT is available on tape for automatic insertion, and less space is occupied on the printed circuit board than the TO-92. Reliability is the same as the TO-92.
FTR	0.65±0.1 2.5±2.5±0.1 1.1 0.45±0.1	SIL type with a height of 3.4 mm and a lead pitch of 2.54 mm.
FTL	0.65Max 2.4±0.2 0.65Max 2.4±0.2 0.5±0.1 0.5±0.1	The FTL is a radial taping version of the highly popular FTR. This enables automatic high-density mounting with a radial insertion machine.
ATR (SC-71 type)	0.65Max	SC-71type with a height of 4.4 mm and a Pc=1W type.



Type	External dimensions (Units : mm)	Features
TO-220FN	\$3.2±0.2	The TO-220FN features the same performance as the TO-220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short-circuiting problems with neighboring components and the chassis. To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.